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New Functional Anthracene Based Liquid Crystals Towards **Organic Optoelectronic Device Applications** A. MOGHNIEH¹, P-E DANJOU², K. FERCHICHI¹, Y. BOUSSOUALEM¹, A. DAOUDI¹



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This study focuses on the development of new multifunctional mesogenic semi-conducting (LC-SC) materials based on 2-amino anthracene and para-hydroxybenzaldehyde¹ (n-OPIA with n=4, 8, 10, 12 and 16). Each material contains a central rigid phenyl-anthracene core, and one terminal flexible alkyloxy chain with different length. These materials are based on the concept of liquid crystal (LC) materials featuring facile processability, highly ordered alignment and effective charge transport. Their thermal behaviors are performed by means of differential scanning calorimetry and polarized optical microscopy, and showed differences on mesomorphic behaviors with respect to the length of the terminal alkyloxy chain. The frontier molecular energy levels were studied by optical spectroscopy and cyclic voltammetry and compared to values obtained via ab initio DFT calculations.

The photoexcitation (λ= 455 nm) of LC Field-Effect Transistors (LC-FETs) based n-OPIA films revealed efficient photo-responsive characteristics in relation to alignment due to alkoxy chain length, indicating their promising potential applications in multifunctional integrated devices.

BST





SS

BEH

PH

ESO



10°C/min showed differences on mesomorphic behaviors with respect to the length of the terminal alkyloxy chain the crystallization temperature is inversely and proportional to the increase in alkoxy chain length.



E_~= 0,555 V

Example of normalised cyclic voltammetry data

obtained for 8- OPIA (2mmol) in 0.1TBAPF₆ in

DCM, degassed with Ar (20 minutes) at 50mV/s

versus Fc/Fc⁺.

E_{HOMO}= -4,955 (eV)



Example of optical absorption spectrum obtained for 8- OPIA (10⁻⁵ M solution in dichloromethane). Inset: absorption for drop-casted thin film of 8-**OPIA (0.5% wt. in chlorobenzene) on quartz** substrate





			(eV)						(eV)	(nm)
4-0PI <i>/</i>	-5,27544	-2,02504	3,25504	-5.03	-2.32	2,71	419,81	2,953	2,86	434
8-OPI <i>4</i>	-5,28034	-2,03102	3,24932	-4.95	-2.7	2,25	418,32	2,963	2.76	451
10- OPIA	-5,27381	-2,02422	3,24959	-5.18	-2.46	2,72	419,49	2,955	2.74	453
12- OPIA	-5,27462	-2,02477	3,24985	-5.01	-2.62	2,39	419,31	2,956	2.76	449
16- OPIA	-5,27354	-2,02368	3,24986	-5.28	-2.61	2,67	419,46	2,955	2.74	453

Frontier molecular energy levels properties for our n-OPIA materials obtained from optical spectroscopy and cyclic voltammetry experiments, and compared to values obtained via ab initio DFT calculations which showed HOMO of n-OPIA align well with gold, that allowed us to use this classic material for electric contacts in order to create a P-type transistor.

n-OPIA	μ _{hole} (cm²/ (V s))	I _{ON} /I _{OFF}	V _{th} (V)
8-OPIA without light	1.8 x 10 ⁻⁴	10 ³	-53
8-OPIA with light	1.9 x 10 ⁻³	35,4	8
10-OPIA without light	1,8 x 10 ⁻⁵	10 ²	-20
10-OPIA with light	8 x 10 ⁻⁴	10 ²	20
12-OPIA without light	1.06 x 10 ⁻⁴	1460	-10
12-OPIA with light	9.8 x 10 ⁻³	32,3	17
16-OPIA without light	1,9 x 10 ⁻⁵	2300	-62
16-OPIA with light	1.5 x 10 ⁻⁴	1830	3

Output characteristics in dark (left) and under illumination (right) (λ = 455 nm) at incident power of 1 mW/cm² of bottom gate FET prepared with drop-casted 8-OPIA film (thickness of about 600 nm). Inset: microscope capture (in polarized light) of the inter-digitated electrode of 8- OPIA-FET (L = 50 μ m, W=18mm) used for measurements.

Relevant properties of charge transport without and with illumination (λ = 455 nm) at incident power of 1 mW/cm² of n-OPIA materials which exhibits reasonable field effect hole mobility in solution-processed thin film.

In summary :

- -Novel homologous series of liquid crystal based phenyl-anthracene with different alkoxy chain length where synthesized and characterized.
- -The thermal behaviors where performed by means of differential scanning calorimetry and polarized optical microscopy.

-Frontier molecular energy levels were studied by optical spectroscopy and cyclic voltammetry and compared to values obtained via ab initio DFT calculations.

-Efficient photo-responsive characteristics indicate their promising potential applications in multifunctional integrated optoelectronic device applications.

RENCES 1) Kondratenko, K.; Carlescu, I.; Danjou, P.-E.; Boussoualem, Y.; Simion, A.; Duponchel, B.; Blach, J. F.; Legrand, C.; Hurduc, N.; Daoudi, A. Novel Organic Semiconductors Based on 2-Amino-Anthracene: Synthesis, Charge Transport and Photo-Conductive Properties. Phys. Chem. Chem. Phys. 2021, 23 (25), REFE 13885–13894. https://doi.org/10.1039/D1CP01427G.

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